

TPS1101, TPS1101Y SINGLE P-CHANNEL ENHANCEMENT-MODE MOSFETS

SLVS079C – DECEMBER 1993 – REVISED AUGUST 1995

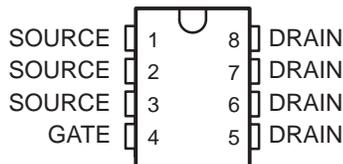
- Low $r_{DS(on)}$. . . 0.09 Ω Typ at $V_{GS} = -10$ V
- 3 V Compatible
- Requires No External V_{CC}
- TTL and CMOS Compatible Inputs
- $V_{GS(th)} = -1.5$ V Max
- Available in Ultrathin TSSOP Package (PW)
- ESD Protection Up to 2 kV per MIL-STD-883C, Method 3015

description

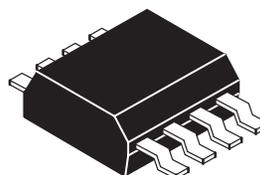
The TPS1101 is a single, low- $r_{DS(on)}$, P-channel, enhancement-mode MOSFET. The device has been optimized for 3-V or 5-V power distribution in battery-powered systems by means of the Texas Instruments LinBiCMOS™ process. With a maximum $V_{GS(th)}$ of -1.5 V and an I_{DSS} of only 0.5 μ A, the TPS1101 is the ideal high-side switch for low-voltage, portable battery-management systems where maximizing battery life is a primary concern. The low $r_{DS(on)}$ and excellent ac characteristics (rise time 5.5 ns typical) of the TPS1101 make it the logical choice for low-voltage switching applications such as power switches for pulse-width-modulated (PWM) controllers or motor/bridge drivers.

The ultrathin thin shrink small-outline package or TSSOP (PW) version fits in height-restricted places where other P-channel MOSFETs cannot. The size advantage is especially important where board height restrictions do not allow for a small-outline integrated circuit (SOIC) package. Such applications include notebook computers, personal digital assistants (PDAs), cellular telephones, and PCMCIA cards. For existing designs, the D-packaged version has a pinout common with other P-channel MOSFETs in SOIC packages.

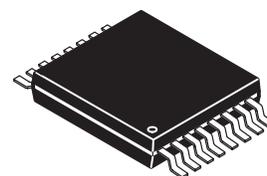
D PACKAGE
(TOP VIEW)



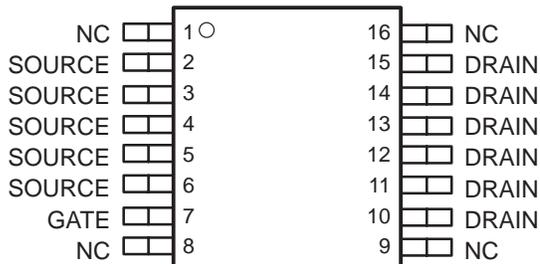
D PACKAGE



PW PACKAGE



PW PACKAGE
(TOP VIEW)



NC – No internal connection

AVAILABLE OPTIONS

T _J	PACKAGED DEVICES†		CHIP FORM (Y)
	SMALL OUTLINE (D)	TSSOP (PW)	
-40°C to 150°C	TPS1101D	TPS1101PWLE	TPS1101Y

† The D package is available taped and reeled. Add an R suffix to device type (e.g., TPS1101DR). The PW package is only available left-end taped and reeled (indicated by the LE suffix on the device type; e.g., TPS1101PWLE). The chip form is tested at 25°C.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS
INSTRUMENTS**

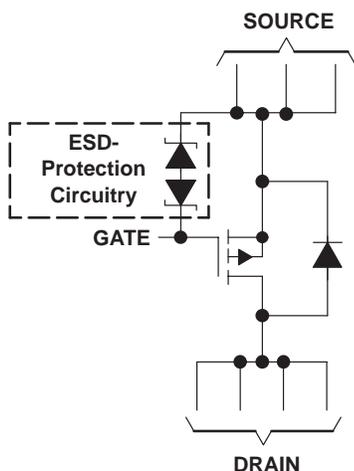
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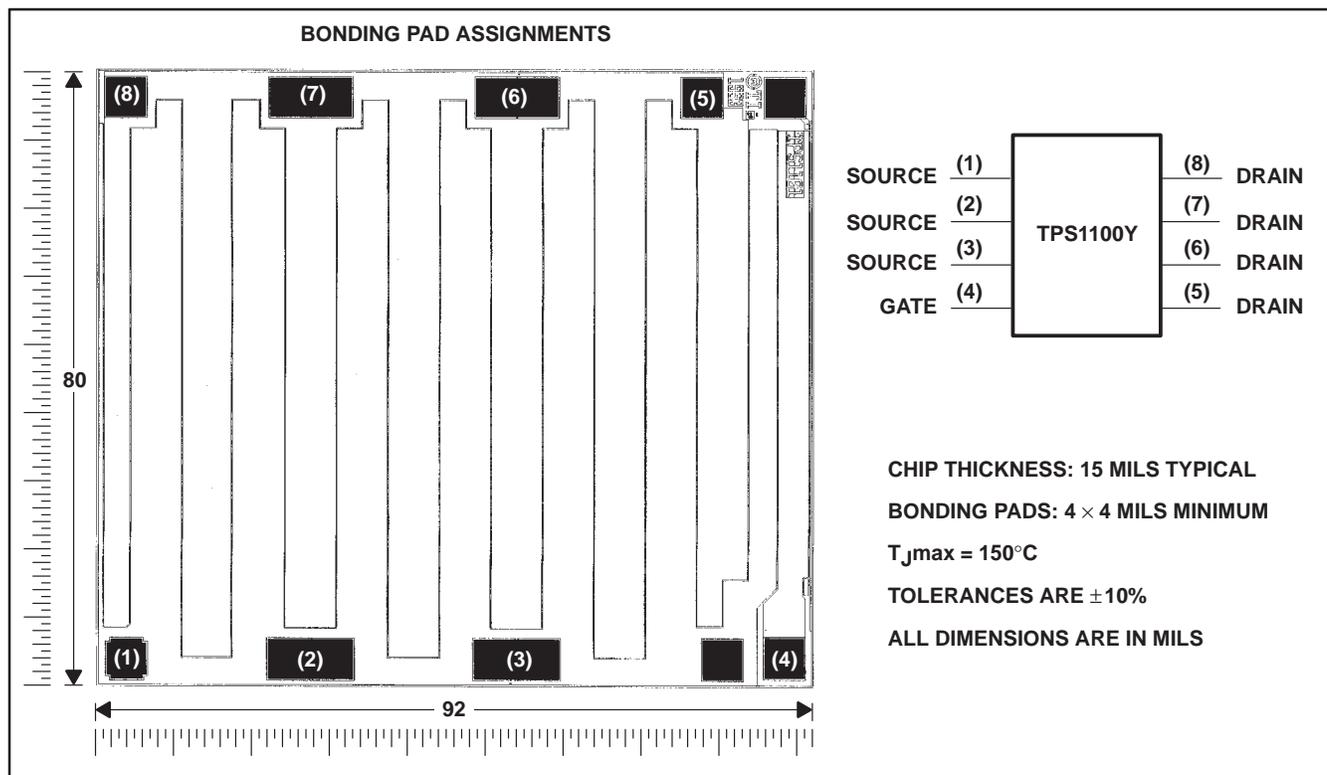
schematic



NOTE A: For all applications, all source terminals should be connected and all drain terminals should be connected.

TPS1101Y chip information

This chip, when properly assembled, displays characteristics similar to the TPS1101. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chips may be mounted with conductive epoxy or a gold-silicon preform.



TPS1101, TPS1101Y

SINGLE P-CHANNEL ENHANCEMENT-MODE MOSFETS

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absolute maximum ratings over operating free-air temperature (unless otherwise noted)[†]

				UNIT	
Drain-to-source voltage, V_{DS}				- 15	V
Gate-to-source voltage, V_{GS}				2 or - 15	V
Continuous drain current ($T_J = 150^\circ\text{C}$), $I_{D\ddagger}$	$V_{GS} = -2.7\text{ V}$	D package	$T_A = 25^\circ\text{C}$	± 0.62	A
			$T_A = 125^\circ\text{C}$	± 0.39	
		PW package	$T_A = 25^\circ\text{C}$	± 0.61	
			$T_A = 125^\circ\text{C}$	± 0.38	
	$V_{GS} = -3\text{ V}$	D package	$T_A = 25^\circ\text{C}$	± 0.88	
			$T_A = 125^\circ\text{C}$	± 0.47	
		PW package	$T_A = 25^\circ\text{C}$	± 0.86	
			$T_A = 125^\circ\text{C}$	± 0.45	
	$V_{GS} = -4.5\text{ V}$	D package	$T_A = 25^\circ\text{C}$	± 1.52	
			$T_A = 125^\circ\text{C}$	± 0.71	
		PW package	$T_A = 25^\circ\text{C}$	± 1.44	
			$T_A = 125^\circ\text{C}$	± 0.67	
$V_{GS} = -10\text{ V}$	D package	$T_A = 25^\circ\text{C}$	± 2.30		
		$T_A = 125^\circ\text{C}$	± 1.04		
	PW package	$T_A = 25^\circ\text{C}$	± 2.18		
		$T_A = 125^\circ\text{C}$	± 0.98		
Pulsed drain current, $I_{D\ddagger}$			$T_A = 25^\circ\text{C}$	± 10	A
Continuous source current (diode conduction), I_S			$T_A = 25^\circ\text{C}$	- 1.1	A
Storage temperature range, T_{stg}				-55 to 150	$^\circ\text{C}$
Operating junction temperature range, T_J				-40 to 150	$^\circ\text{C}$
Operating free-air temperature range, T_A				-40 to 125	$^\circ\text{C}$
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds				260	$^\circ\text{C}$

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[‡] Maximum values are calculated using a derating factor based on $R_{\theta JA} = 158^\circ\text{C}/\text{W}$ for the D package and $R_{\theta JA} = 176^\circ\text{C}/\text{W}$ for the PW package. These devices are mounted on an FR4 board with no special thermal considerations.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR [‡] ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D	791 mW	6.33 mW/ $^\circ\text{C}$	506 mW	411 mW	158 mW
PW	710 mW	5.68 mW/ $^\circ\text{C}$	454 mW	369 mW	142 mW

[‡] Maximum values are calculated using a derating factor based on $R_{\theta JA} = 158^\circ\text{C}/\text{W}$ for the D package and $R_{\theta JA} = 176^\circ\text{C}/\text{W}$ for the PW package. These devices are mounted on an FR4 board with no special thermal considerations.

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electrical characteristics at $T_J = 25^\circ\text{C}$ (unless otherwise noted)

static

PARAMETER	TEST CONDITIONS	TPS1101			TPS1101Y			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
$V_{GS(th)}$ Gate-to-source threshold voltage	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-1	-1.25	-1.5	-1.25			V
V_{SD} Source-to-drain voltage (diode-forward voltage) [†]	$I_S = -1 \text{ A}$, $V_{GS} = 0 \text{ V}$	-1.04			-1.04			V
I_{GSS} Reverse gate current, drain short circuited to source	$V_{DS} = 0 \text{ V}$, $V_{GS} = -12 \text{ V}$	±100						nA
I_{DSS} Zero-gate-voltage drain current	$V_{DS} = -12 \text{ V}$, $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		-0.5				μA
		$T_J = 125^\circ\text{C}$		-10				
$r_{DS(on)}$ Static drain-to-source on-state resistance [†]	$V_{GS} = -10 \text{ V}$, $I_D = -2.5 \text{ A}$	90			90			m Ω
	$V_{GS} = -4.5 \text{ V}$, $I_D = -1.5 \text{ A}$	134	190	134				
	$V_{GS} = -3 \text{ V}$, $I_D = -0.5 \text{ A}$	198	310	198				
	$V_{GS} = -2.7 \text{ V}$, $I_D = -0.5 \text{ A}$	232	400	232				
g_{fs} Forward transconductance [†]	$V_{DS} = -10 \text{ V}$, $I_D = -2 \text{ A}$	4.3			4.3			S

[†] Pulse test: pulse duration $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

dynamic

PARAMETER	TEST CONDITIONS	TPS1101, TPS1101Y			UNIT
		MIN	TYP	MAX	
Q_g Total gate charge	$V_{DS} = -10 \text{ V}$, $V_{GS} = -10 \text{ V}$, $I_D = -1 \text{ A}$	11.25			nC
Q_{gs} Gate-to-source charge		1.5			
Q_{gd} Gate-to-drain charge		2.6			
$t_{d(on)}$ Turn-on delay time	$V_{DD} = -10 \text{ V}$, $R_L = 10 \Omega$, $R_G = 6 \Omega$, See Figures 1 and 2, $I_D = -1 \text{ A}$	6.5			ns
$t_{d(off)}$ Turn-off delay time		19			ns
t_r Rise time		5.5			ns
t_f Fall time		13			
$t_{rr(SD)}$ Source-to-drain reverse recovery time	$I_F = 5.3 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$	16			

PARAMETER MEASUREMENT INFORMATION

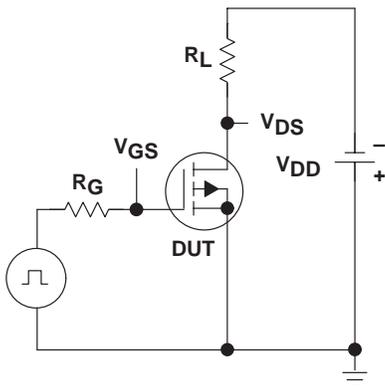


Figure 1. Switching-Time Test Circuit

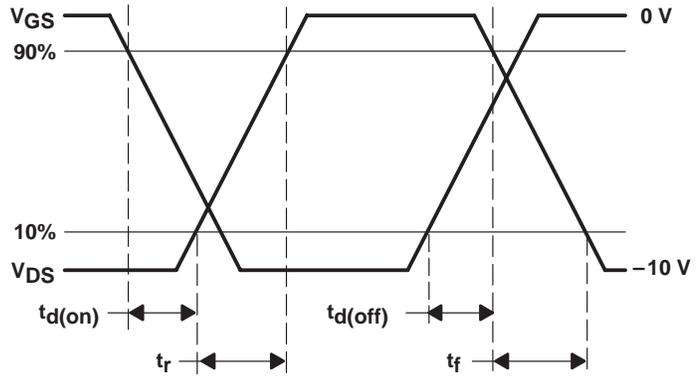


Figure 2. Switching-Time Waveforms

TYPICAL CHARACTERISTICS

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Drain current	vs Gate-to-source voltage	4
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Static drain-to-source on-state resistance (normalized)	vs Junction temperature	7
Source-to-drain diode current	vs Source-to-drain voltage	8
Static drain-to-source on-state resistance	vs Gate-to-source voltage	9
Gate-to-source threshold voltage	vs Junction temperature	10
Gate-to-source voltage	vs Gate charge	11

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TYPICAL CHARACTERISTICS

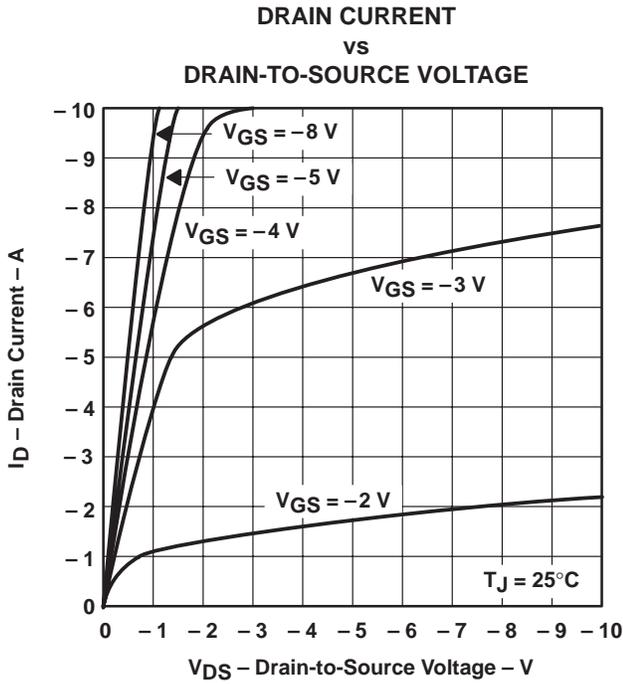


Figure 3

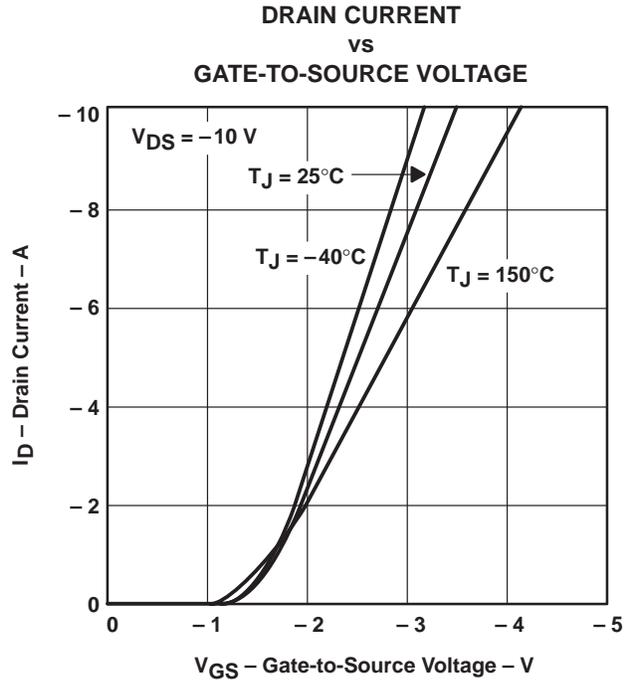


Figure 4

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs DRAIN CURRENT

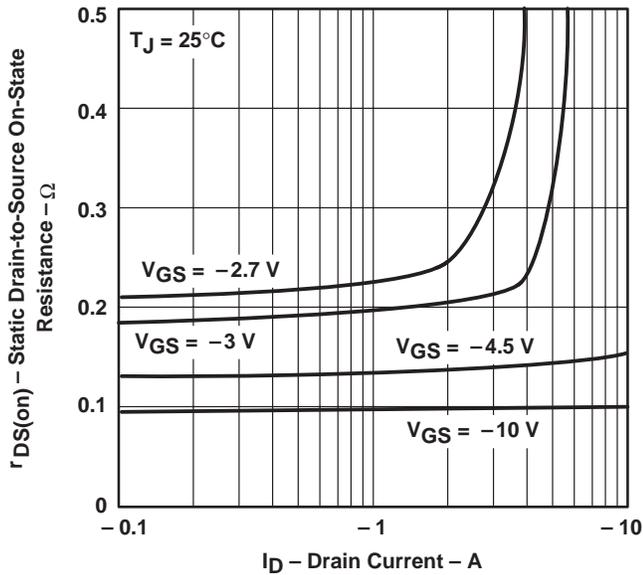
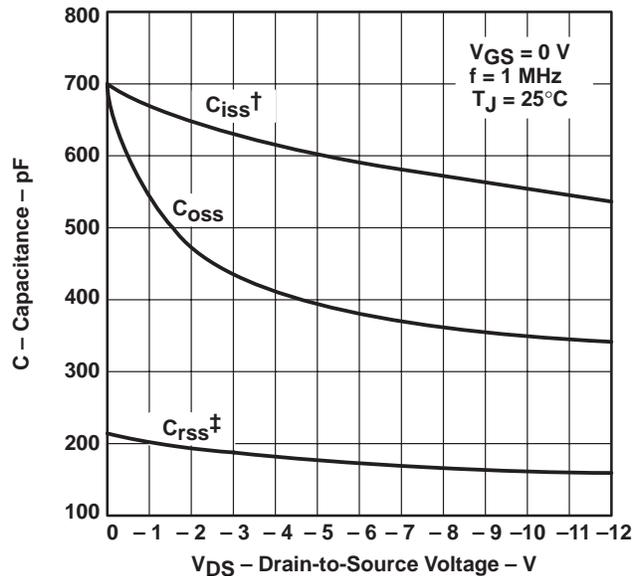


Figure 5

CAPACITANCE† vs DRAIN-TO-SOURCE VOLTAGE



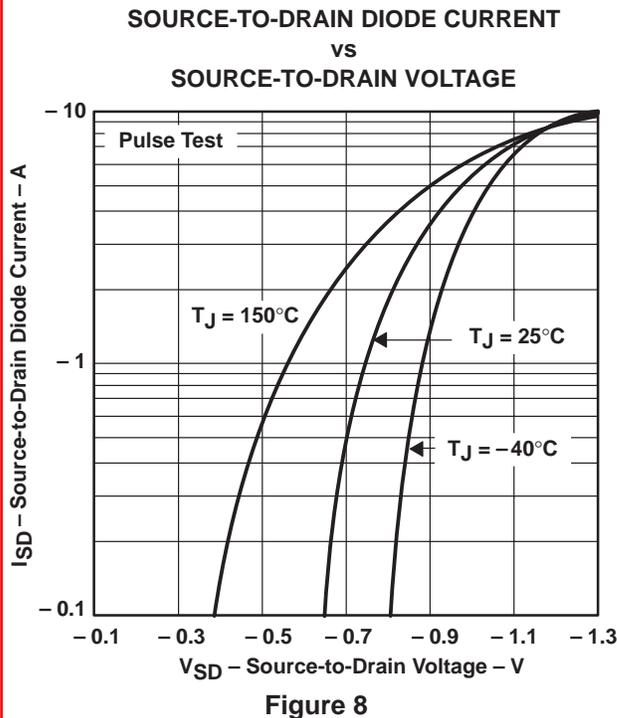
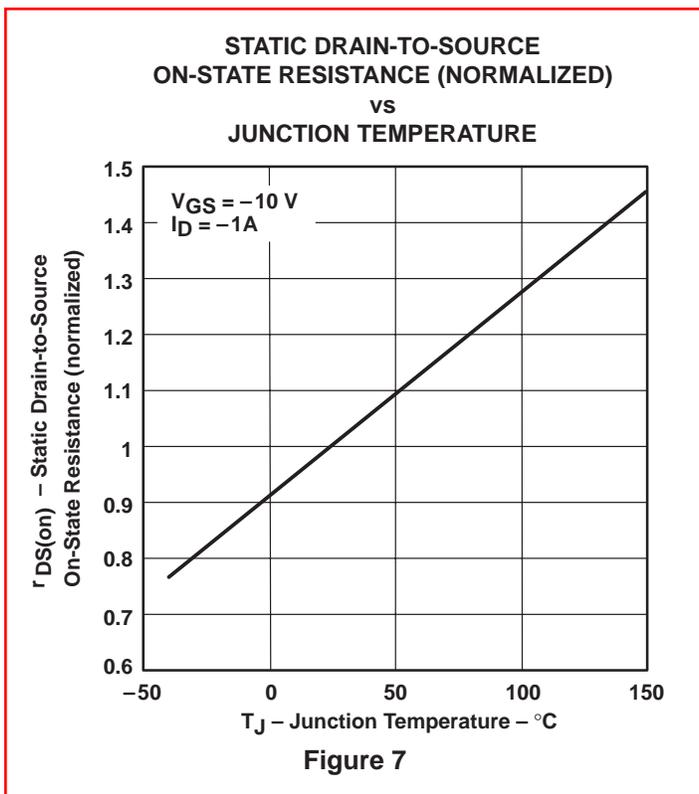
$$† C_{iss} = C_{gs} + C_{gd}, C_{ds(\text{shorted})}$$

$$‡ C_{rss} = C_{gd}, C_{oss} = C_{ds} + \frac{C_{gs} C_{gd}}{C_{gs} + C_{gd}} \approx C_{ds} + C_{gd}$$

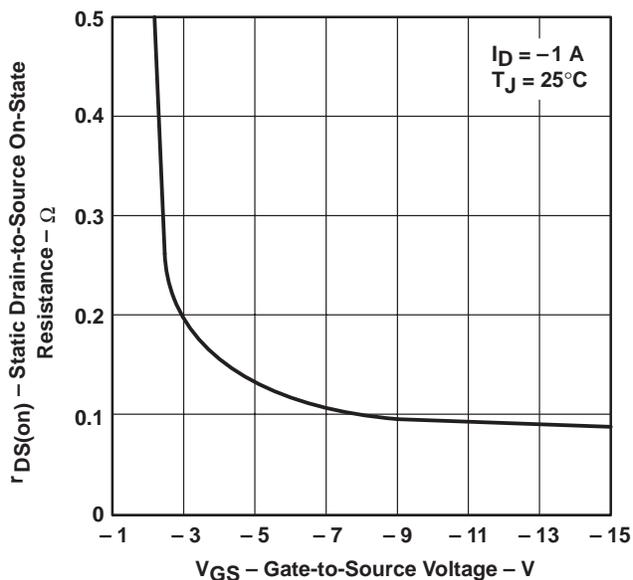
Figure 6



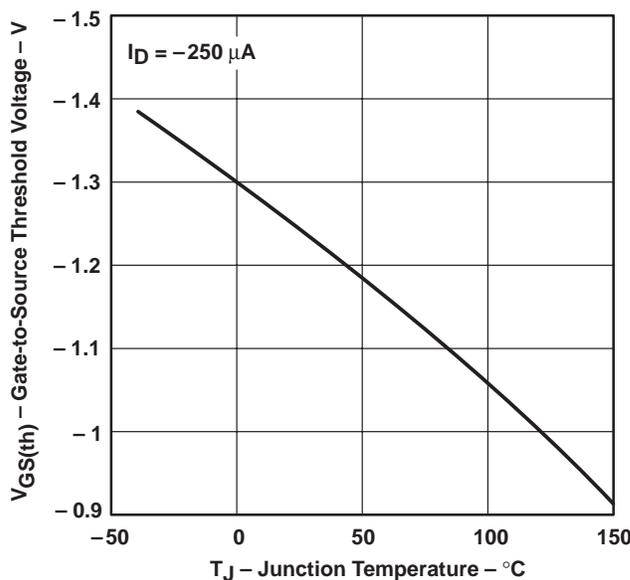
TYPICAL CHARACTERISTICS



STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs GATE-TO-SOURCE VOLTAGE



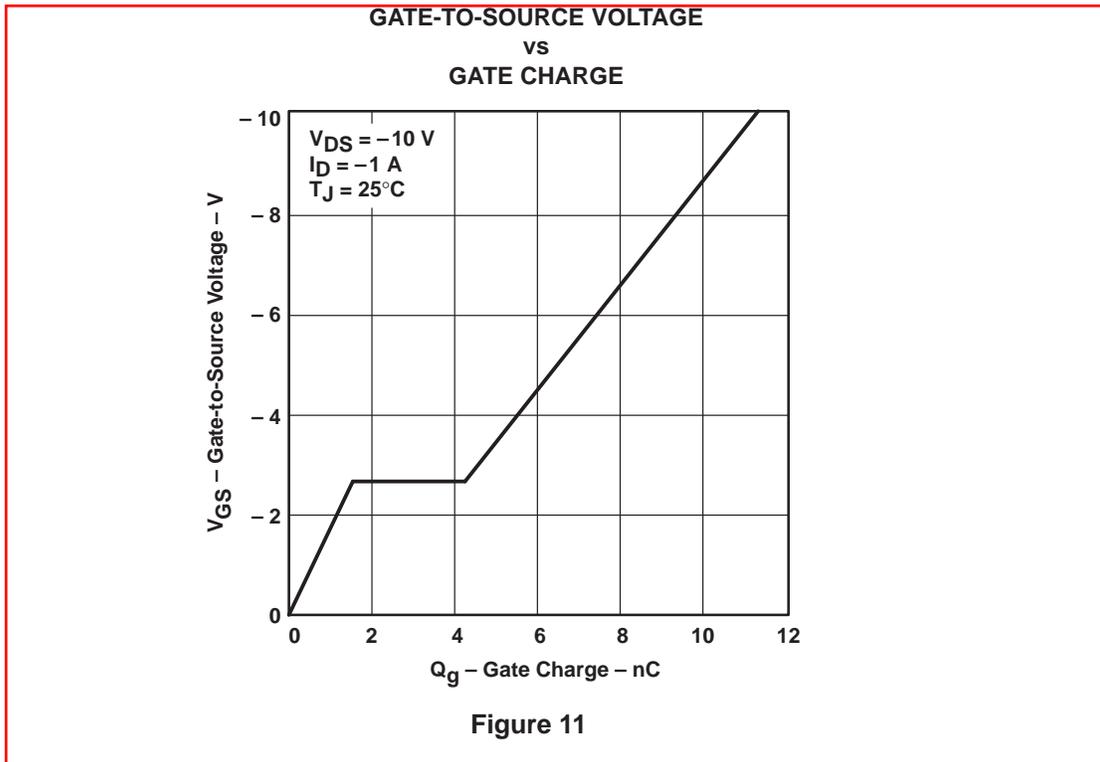
GATE-TO-SOURCE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE



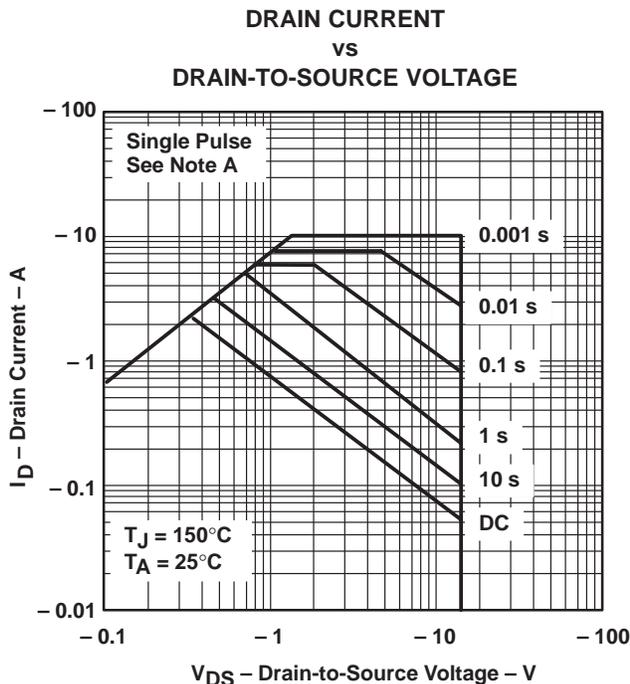
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TYPICAL CHARACTERISTICS

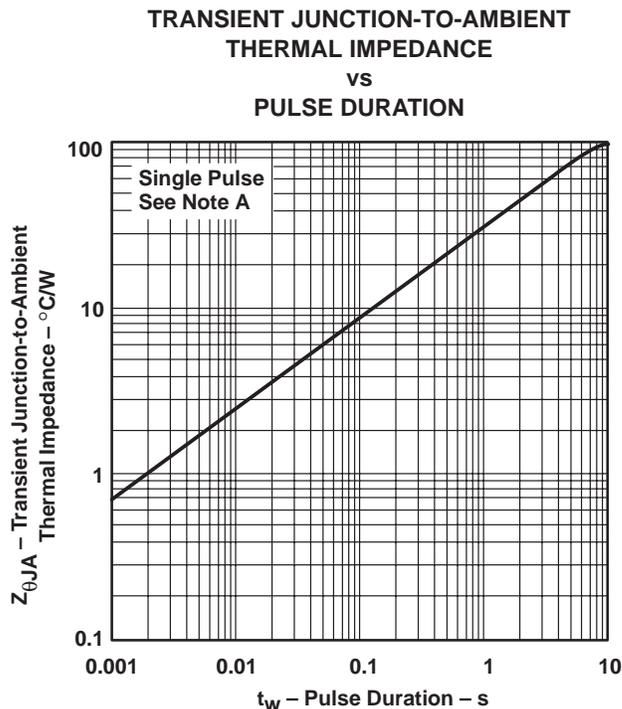


THERMAL INFORMATION



NOTE A: Values are for the D package and are FR4-board-mounted only.

Figure 12



NOTE A: Values are for the D package and are FR4-board-mounted only.

Figure 13

APPLICATION INFORMATION

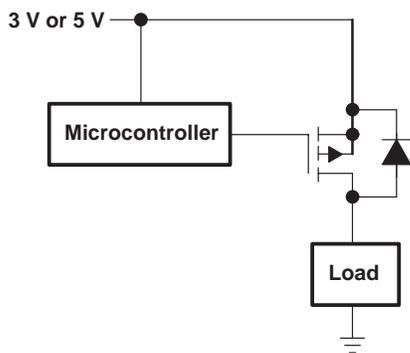


Figure 14. Notebook Load Management

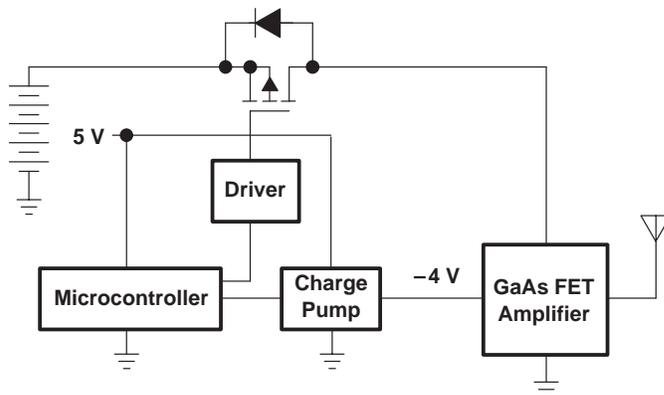


Figure 15. Cellular Phone Output Drive

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS1101D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		1101	Samples
TPS1101DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		1101	Samples
TPS1101PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		PS1101	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

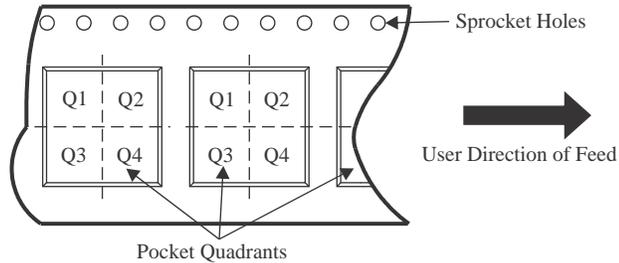
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


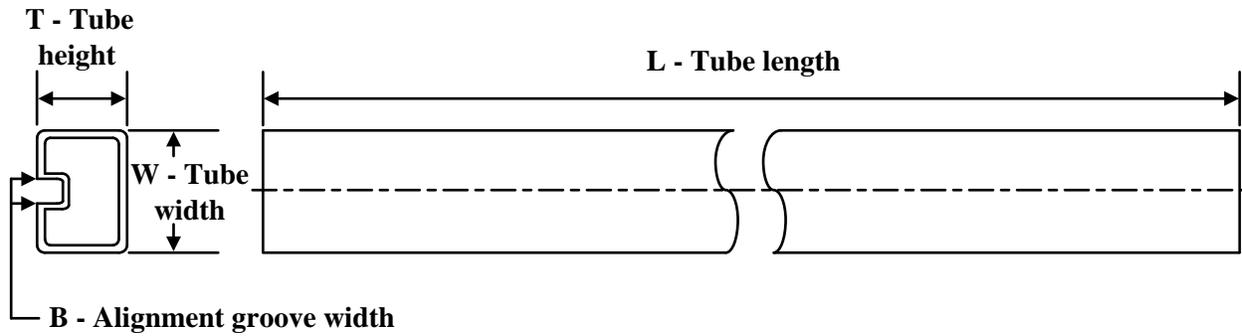
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS1101DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS1101PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS1101DR	SOIC	D	8	2500	340.5	338.1	20.6
TPS1101PWR	TSSOP	PW	16	2000	356.0	356.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
TPS1101D	D	SOIC	8	75	507	8	3940	4.32

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